

General Description

- Trench Power MOSFET technology
- Low $R_{DS(ON)}$
- Low Gate Charge
- RoHS and Halogen-Free Compliant

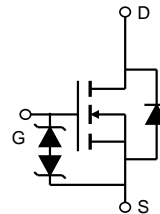
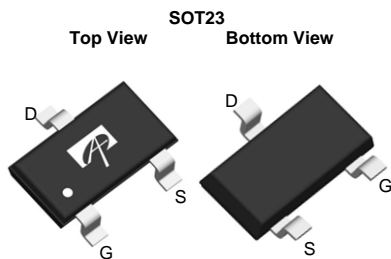
Applications

- Ideal for Load Switching

Product Summary

V_{DS}	30V
I_D (at $V_{GS}=10V$)	4A
$R_{DS(ON)}$ (at $V_{GS}=10V$)	< 50m Ω
$R_{DS(ON)}$ (at $V_{GS}=4.5V$)	< 57m Ω
$R_{DS(ON)}$ (at $V_{GS}=2.5V$)	< 72m Ω

ESD protection



Orderable Part Number	Package Type	Form	Minimum Order Quantity
AOSS32338C	SOT23-3	Tape & Reel	3000

Absolute Maximum Ratings $T_A=25^\circ\text{C}$ unless otherwise noted

Parameter	Symbol	Maximum	Units
Drain-Source Voltage	V_{DS}	30	V
Gate-Source Voltage	V_{GS}	± 12	V
Continuous Drain Current	I_D	4	A
Current		3.1	
Pulsed Drain Current ^C	I_{DM}	24	
Power Dissipation ^B	P_D	1.3	W
		0.8	
Junction and Storage Temperature Range	T_J, T_{STG}	-55 to 150	$^\circ\text{C}$

Thermal Characteristics

Parameter	Symbol	Typ	Max	Units
Maximum Junction-to-Ambient ^A	$R_{\theta JA}$	70	90	$^\circ\text{C/W}$
Maximum Junction-to-Ambient ^{A,D}		100	125	
Maximum Junction-to-Lead	$R_{\theta JL}$	63	80	$^\circ\text{C/W}$

Electrical Characteristics (T_J=25°C unless otherwise noted)

Symbol	Parameter	Conditions	Min	Typ	Max	Units
STATIC PARAMETERS						
BV _{DSS}	Drain-Source Breakdown Voltage	ID=250μA, VGS=0V	30			V
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} =30V, V _{GS} =0V T _J =55°C			1 5	μA
I _{GSS}	Gate-Body leakage current	V _{DS} =0V, V _{GS} =±12V			±10	μA
V _{GS(th)}	Gate Threshold Voltage	V _{DS} =V _{GS} , I _D =250μA	0.5	1	1.5	V
R _{DS(on)}	Static Drain-Source On-Resistance	V _{GS} =10V, I _D =4A T _J =125°C		40 58	50 73	mΩ
		V _{GS} =4.5V, I _D =4A		42	57	
		V _{GS} =2.5V, I _D =3.5A		50	72	mΩ
g _{FS}	Forward Transconductance	V _{DS} =5V, I _D =4A		20		S
V _{SD}	Diode Forward Voltage	I _S =1A, V _{GS} =0V		0.7	1	V
I _S	Maximum Body-Diode Continuous Current				2	A
DYNAMIC PARAMETERS						
C _{iss}	Input Capacitance	V _{GS} =0V, V _{DS} =15V, f=1MHz		340		pF
C _{oss}	Output Capacitance			30		pF
C _{riss}	Reverse Transfer Capacitance			25		pF
R _g	Gate resistance	f=1MHz	4	8	12	Ω
SWITCHING PARAMETERS						
Q _{g(10V)}	Total Gate Charge	V _{GS} =10V, V _{DS} =15V, I _D =4A		8	16	nC
Q _{g(4.5V)}	Total Gate Charge			4	8	nC
Q _{gs}	Gate Source Charge			1		nC
Q _{gd}	Gate Drain Charge			1.2		nC
t _{D(on)}	Turn-On Delay Time	V _{GS} =10V, V _{DS} =15V, R _L =3.75Ω, R _{GEN} =3Ω		2.5		ns
t _r	Turn-On Rise Time			3		ns
t _{D(off)}	Turn-Off Delay Time			30		ns
t _f	Turn-Off Fall Time			5		ns
t _{rr}	Body Diode Reverse Recovery Time	I _F =4A, di/dt=500A/μs		5.5		ns
Q _{rr}	Body Diode Reverse Recovery Charge	I _F =4A, di/dt=500A/μs		4		nC

A. The value of R_{θJA} is measured with the device mounted on 1in² FR-4 board with 2oz. Copper, in a still air environment with T_A=25° C. The value in any given application depends on the user's specific board design.

B. The power dissipation P_D is based on T_{J(MAX)}=150° C, using ≤ 10s junction-to-ambient thermal resistance.

C. Repetitive rating, pulse width limited by junction temperature T_{J(MAX)}=150° C. Ratings are based on low frequency and duty cycles to keep initial T_J=25° C.

D. The R_{θJA} is the sum of the thermal impedance from junction to lead R_{θJL} and lead to ambient.

E. The static characteristics in Figures 1 to 6 are obtained using <300μs pulses, duty cycle 0.5% max.

F. These curves are based on the junction-to-ambient thermal impedance which is measured with the device mounted on 1in² FR-4 board with 2oz. Copper, assuming a maximum junction temperature of T_{J(MAX)}=150° C. The SOA curve provides a single pulse rating.

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TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

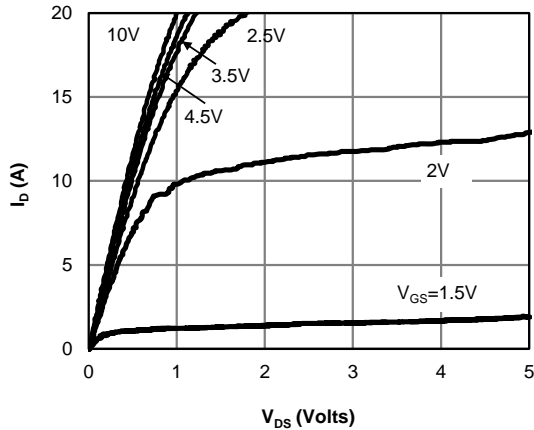


Figure 1: On-Region Characteristics (Note E)

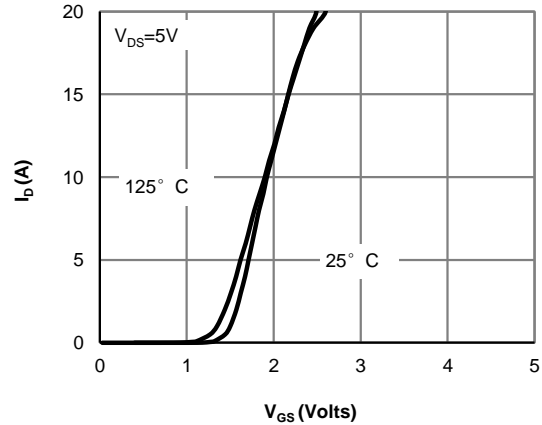


Figure 2: Transfer Characteristics (Note E)

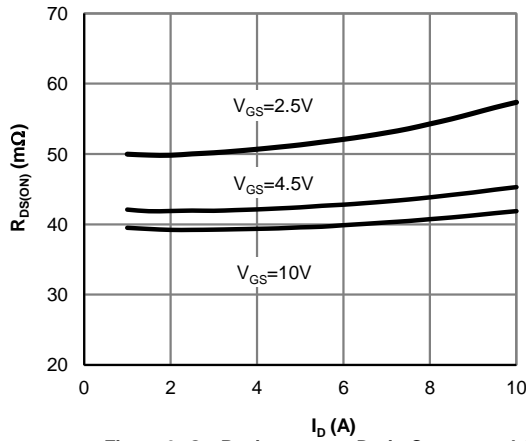


Figure 3: On-Resistance vs. Drain Current and Gate Voltage (Note E)

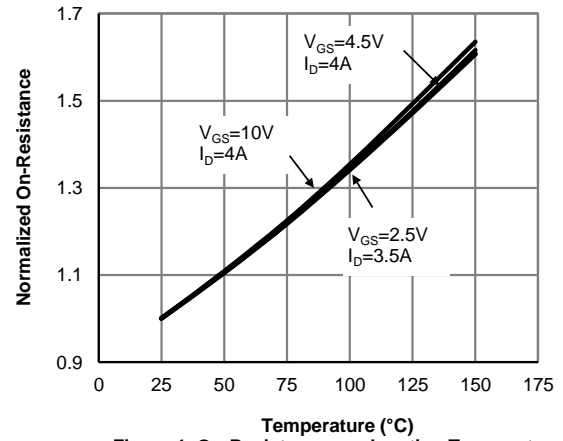


Figure 4: On-Resistance vs. Junction Temperature (Note E)

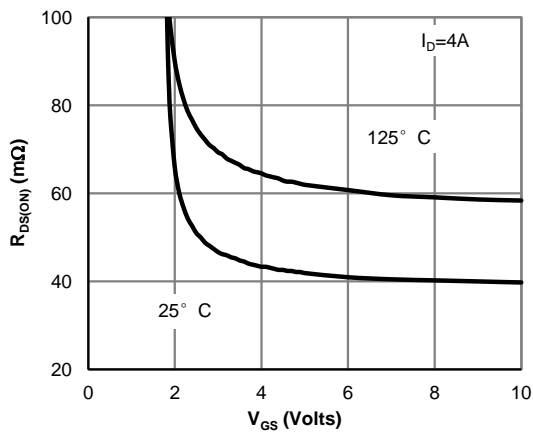


Figure 5: On-Resistance vs. Gate-Source Voltage (Note E)

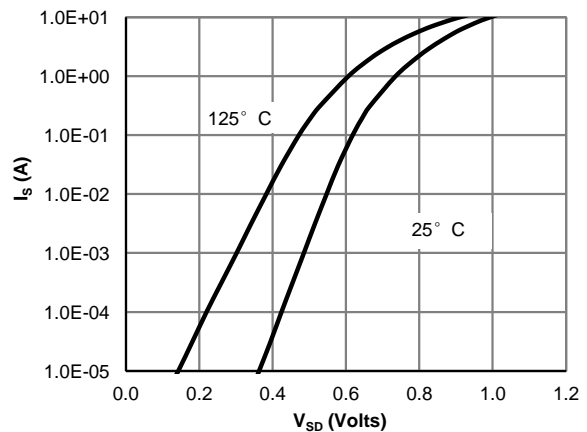


Figure 6: Body-Diode Characteristics (Note E)

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

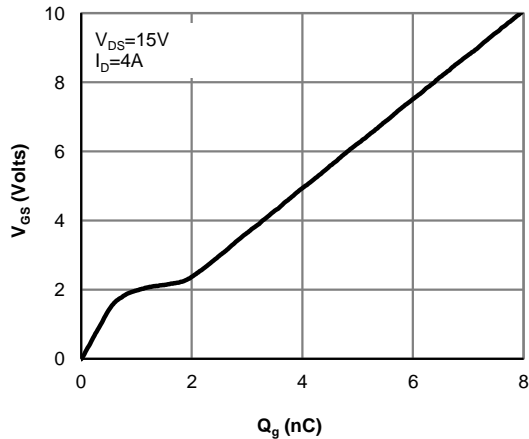


Figure 7: Gate-Charge Characteristics

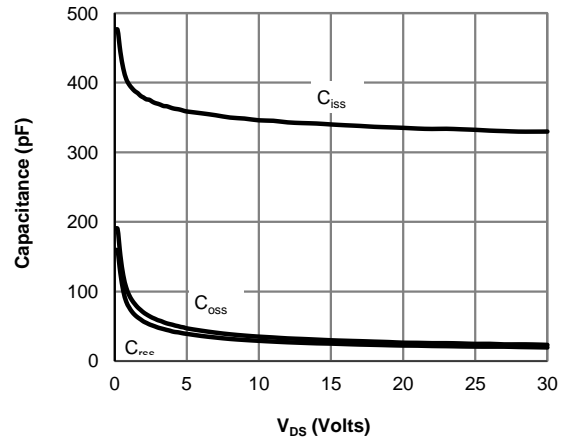


Figure 8: Capacitance Characteristics

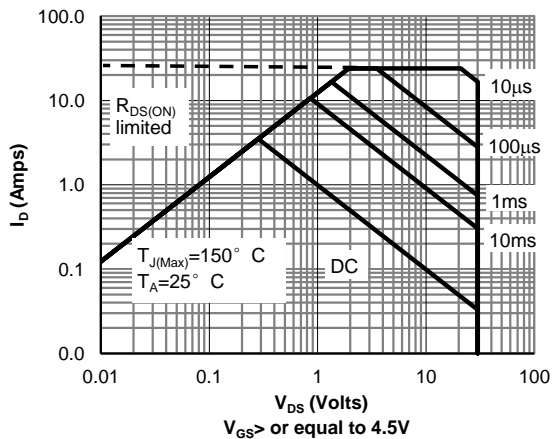


Figure 9: Maximum Forward Biased Safe Operating Area (Note F)

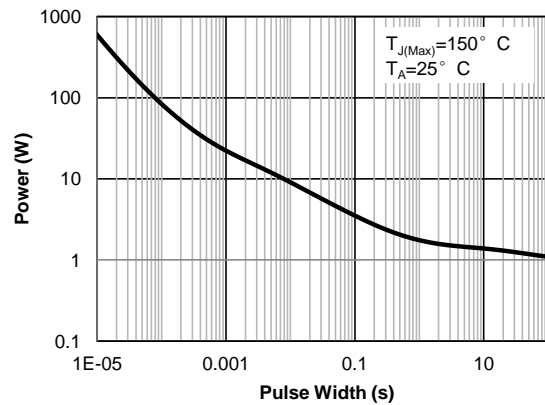


Figure 10: Single Pulse Power Rating Junction-to-Ambient (Note F)

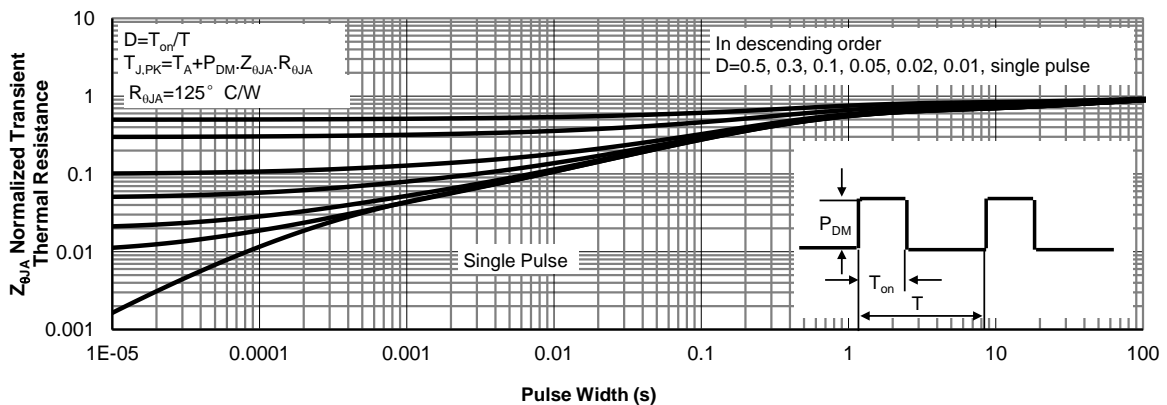


Figure 11: Normalized Maximum Transient Thermal Impedance (Note F)

Figure A: Gate Charge Test Circuit & Waveforms

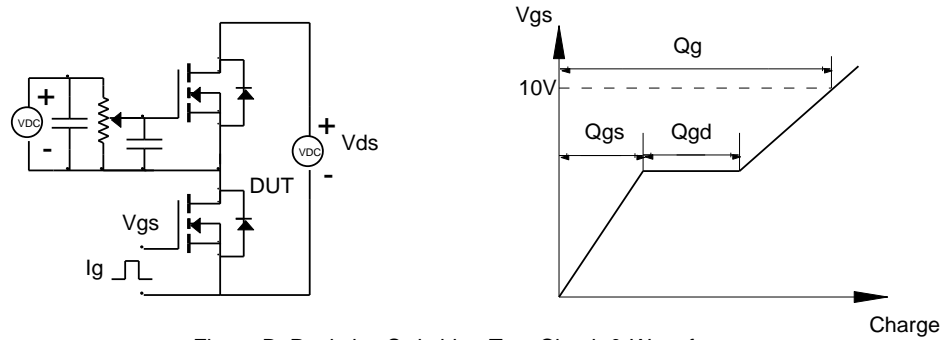


Figure B: Resistive Switching Test Circuit & Waveforms

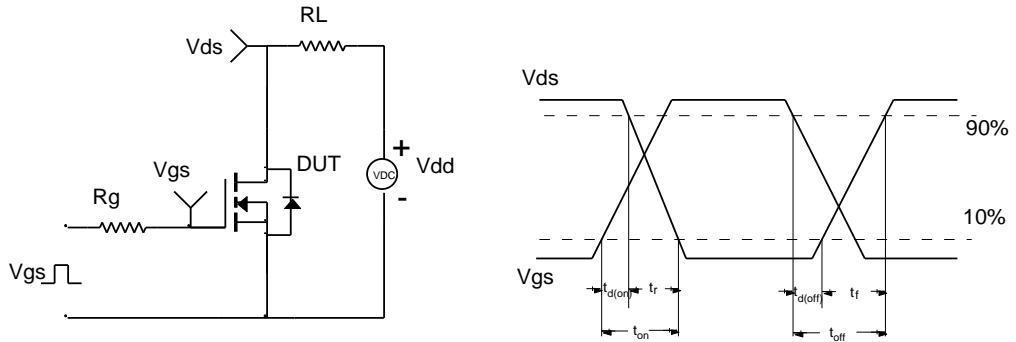


Figure C: Unclamped Inductive Switching (UIS) Test Circuit & Waveforms

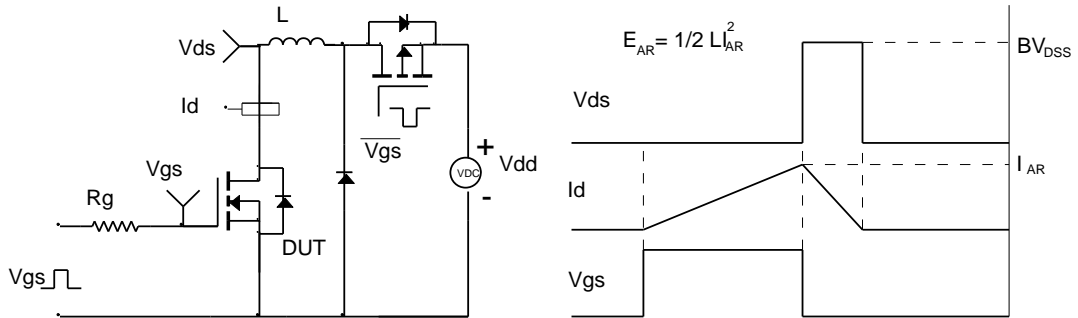
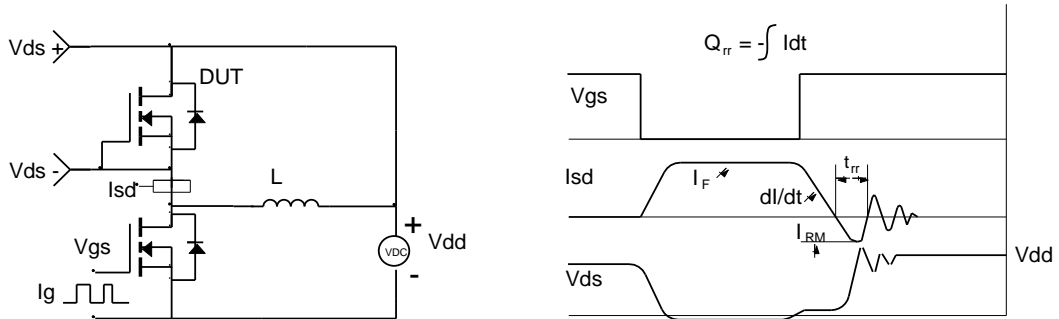


Figure D: Diode Recovery Test Circuit & Waveforms



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